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Chemical Engineering

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Advanced Research Center for Green Materials Science and Technology  
MOE 113L9006

# Utilization of Conjugated Self-Assembled Molecules in Photosynaptic Transistors for Achieving Ultralow Energy Consumption

Date: 2024/02/20

Speaker: Ya-Shuan Wu

Advisor: Prof. Wen-Chang Chen

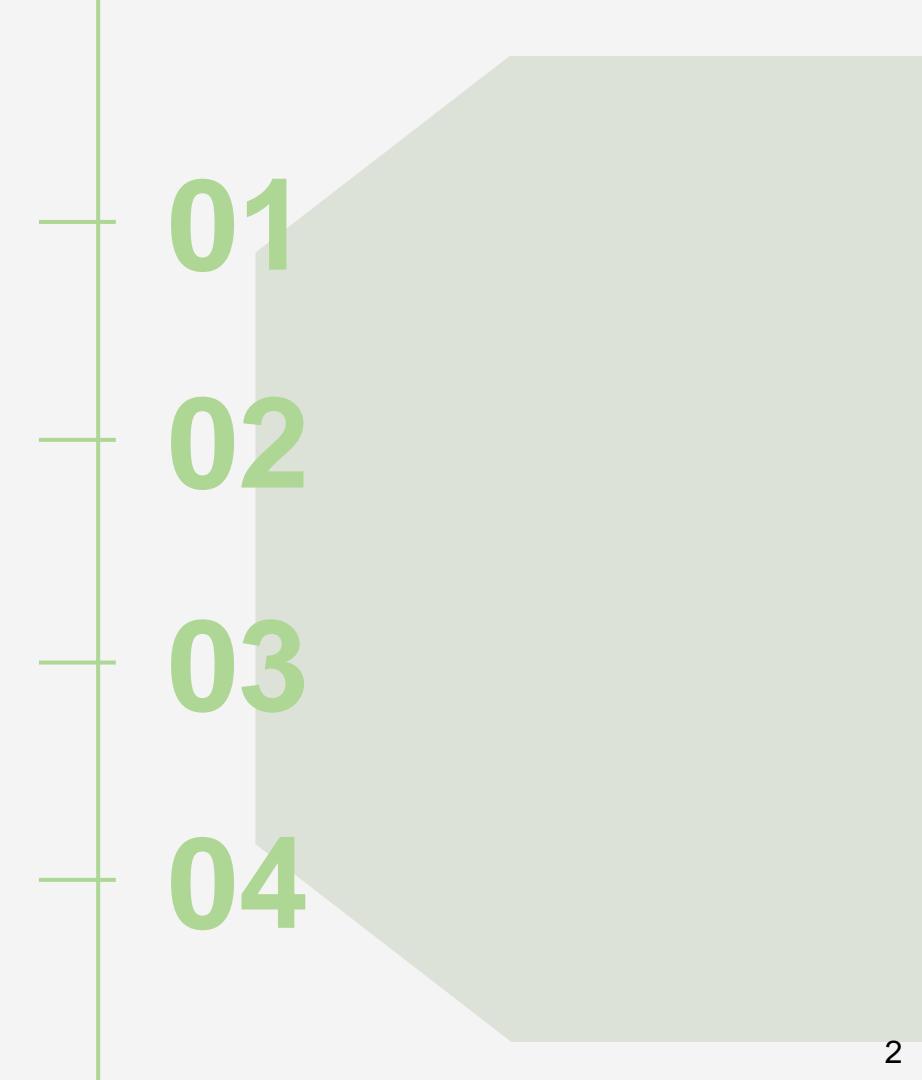
# Outline

Introduction

Synthesis & Device Fabrication

Analysis & Electrical Characteristics

Conclusion



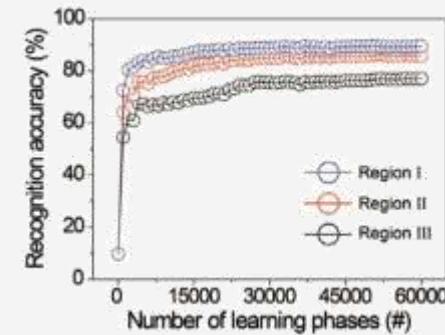
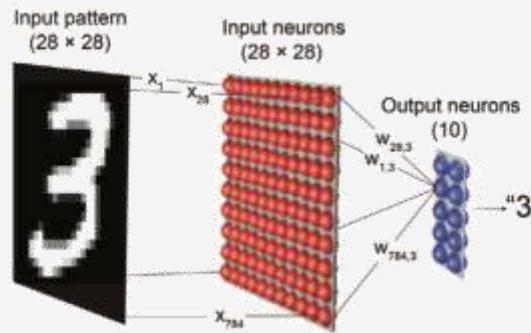
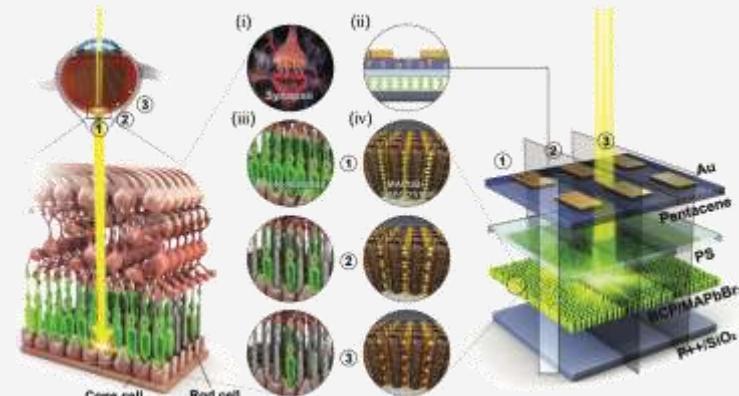
# Introduction

## von Neumann bottleneck:

- ✓ Separation between memory and computing system
- ✓ Low data capacity and long processing time

## Photosynaptic transistor:

- ✓ Integrate sensing and information storage
- ✓ Mimic human learning behavior
- ✓ Light  $\Rightarrow$  noncontact programming



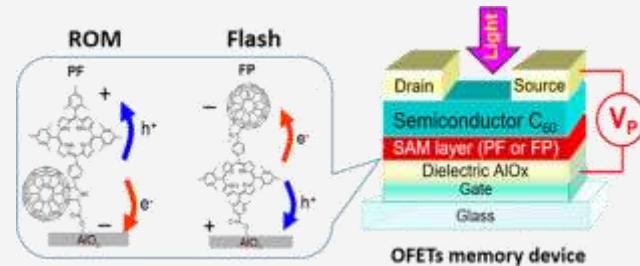
Lee, K., Han, H., Kim, Y., Park, J., Jang, S., Lee, H., ... & Park, C. (2021). Retina-Inspired Structurally Tunable Synaptic Perovskite Nanocones. *Advanced Functional Materials*, 31(52), 2105596.

# Introduction

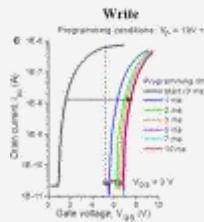
## Self-assembled molecules (SAMs):

- ✓ Surface modification and defect passivation
- ✓ Formation of an ultrathin layer
- ✓ High capacitance and low current leakage

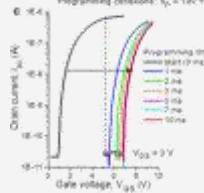
## ● Sequence of Molecular Structures



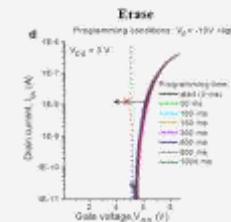
Read-only memory devices using monolayer of PF dyad



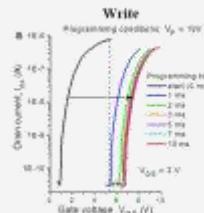
Write



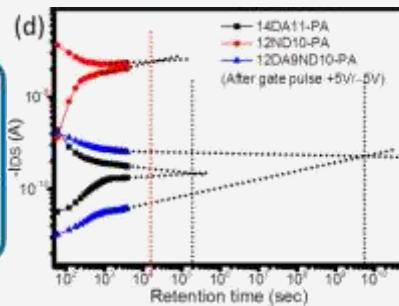
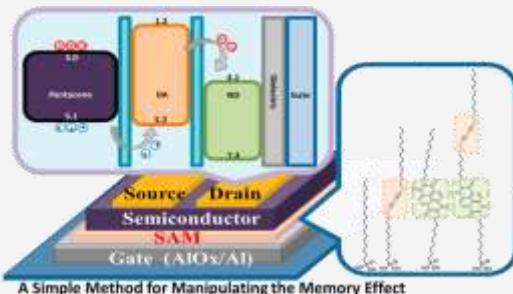
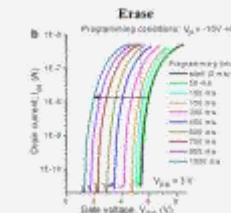
Erase



Flash memory devices using monolayer of FP dyad



Write



Tseng, C. W., Huang, D. C., & Tao, Y. T. (2015). Organic transistor memory with a charge storage molecular double-floating-gate monolayer. *ACS applied materials & interfaces*, 7(18), 9767-9775.

Frolova, L. A., Furmansky, Y., Shestakov, A. F., Emelianov, N. A., Liddell, P. A., Gust, D., ... & Troshin, P. A. (2022). Advanced Nonvolatile Organic Optical Memory Using Self-Assembled Monolayers of Porphyrin–Fullerene Dyads. *ACS applied materials & interfaces*, 14(13), 15461-15467.

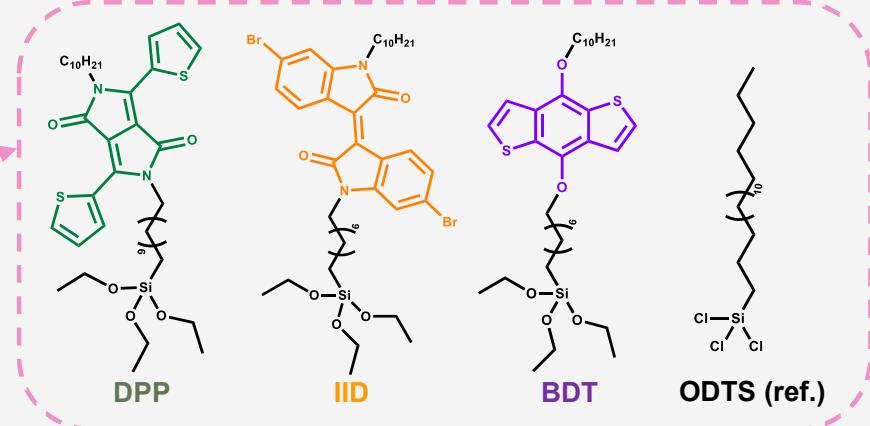
# Introduction

## Objective:

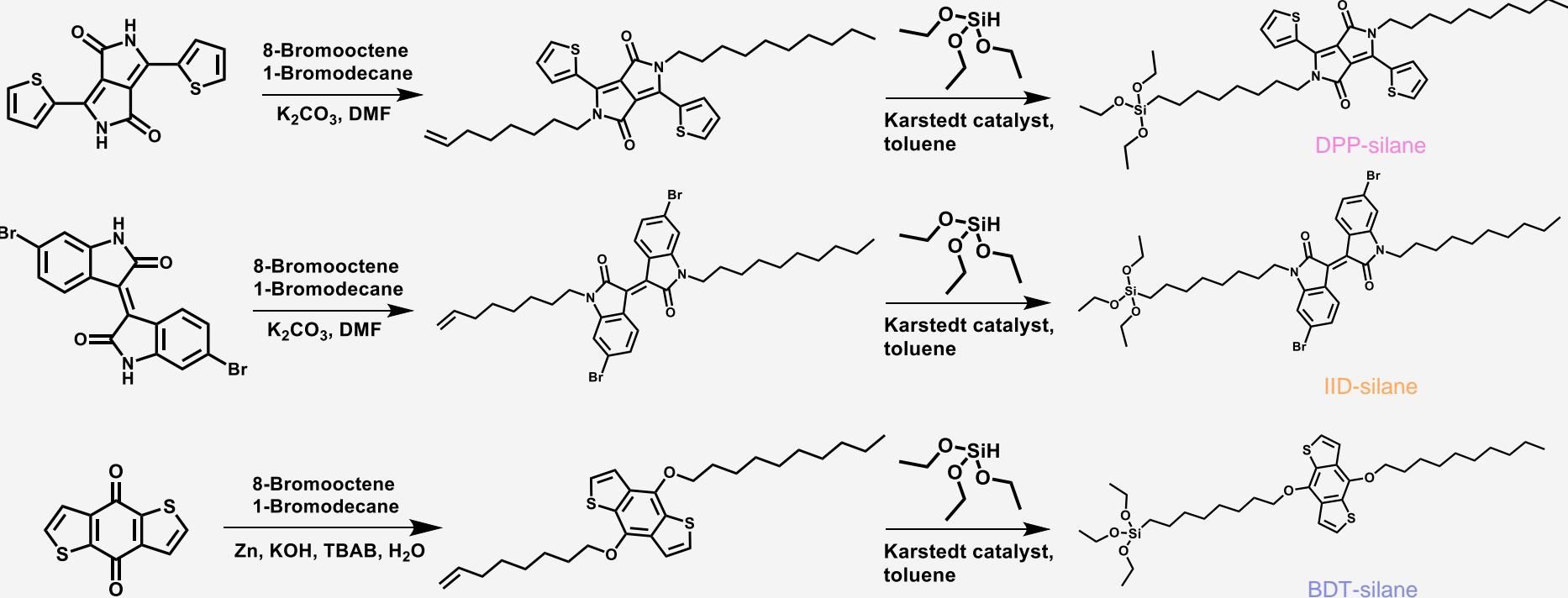
- ✓ Simple device architecture with photoactive SAMs
- ✓ Low energy consumption
- ✓ Photosynaptic transistor

## Comparison with OTDS:

- ✓ Chains with equal number of carbon atoms
- ✓ Existence of chromophore
- ✓ Ability for charge storage

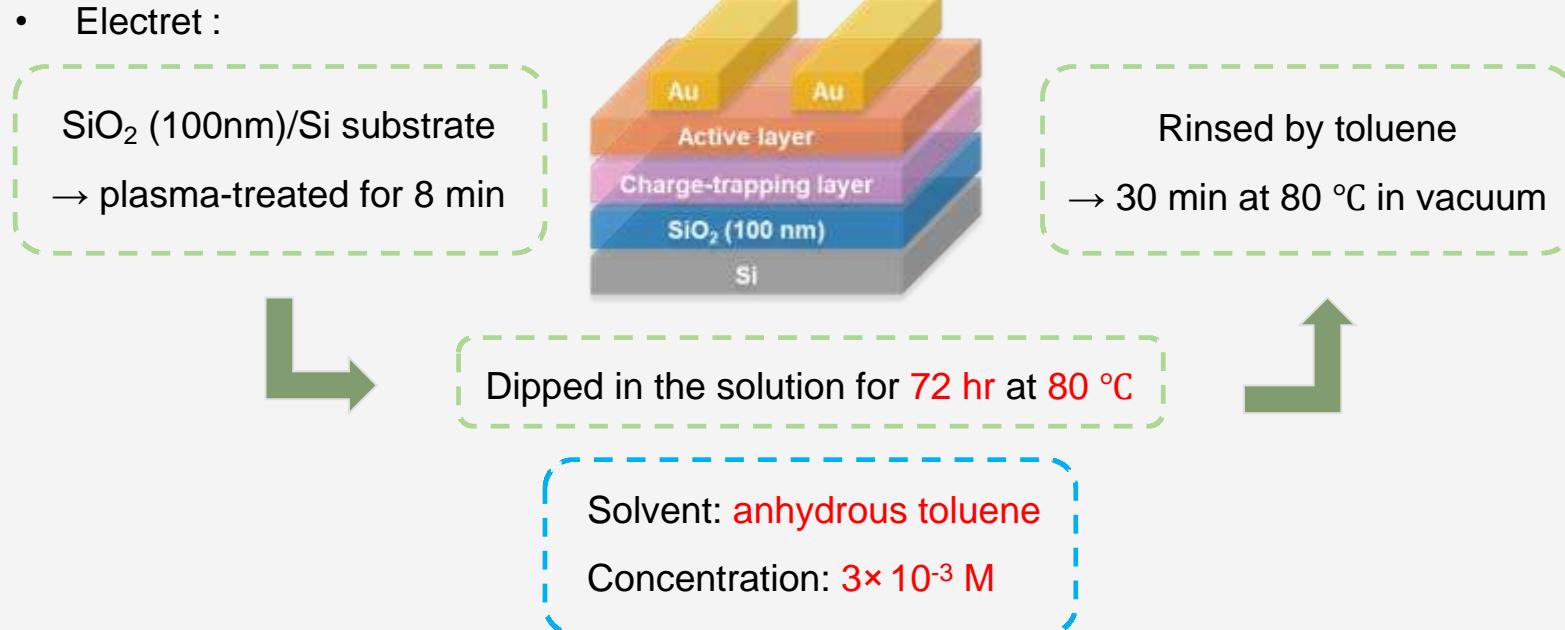


# Synthesis

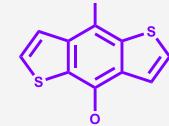
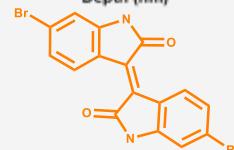
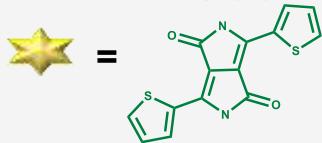
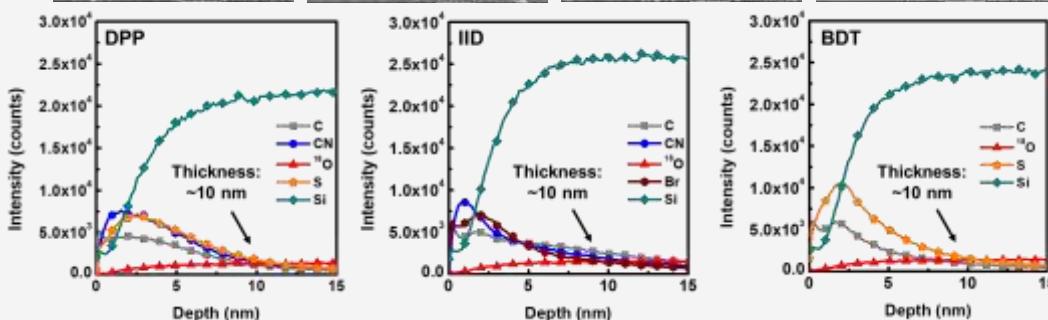
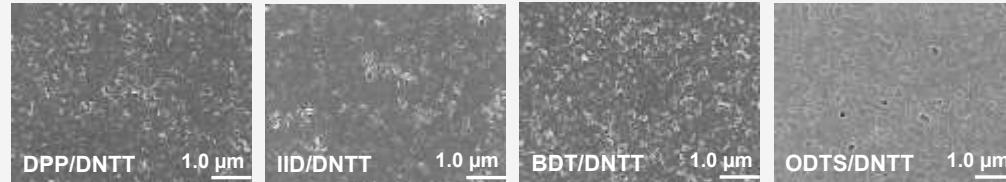
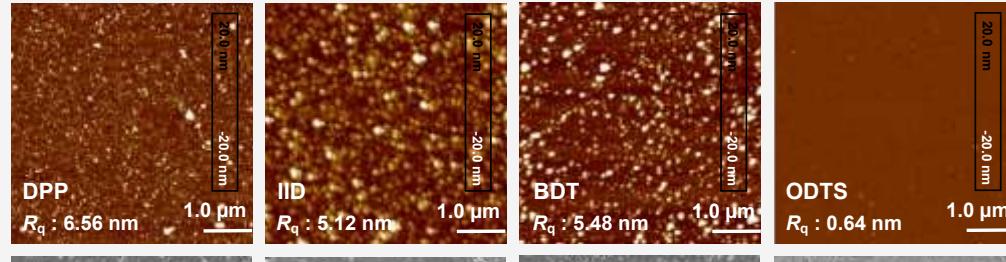


# Device Fabrication

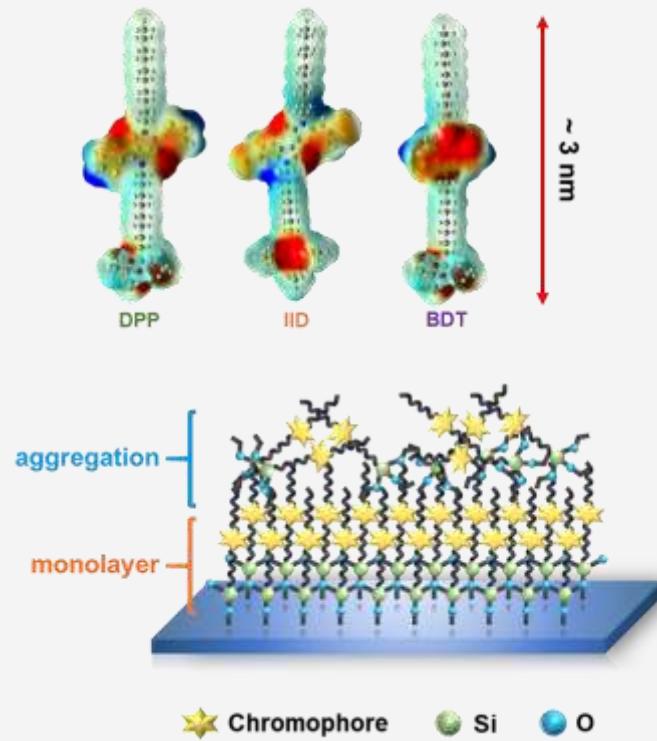
- Electrodes : 70 nm thick by deposition
- Active layer : 50 nm thick by deposition
- Electret :



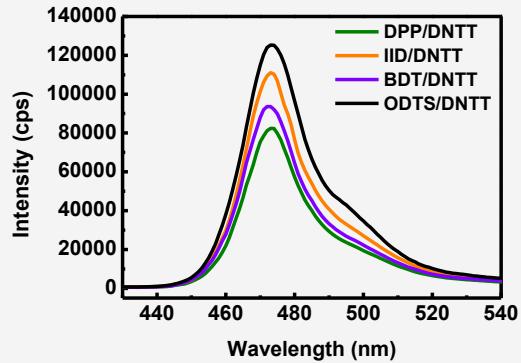
# Morphology Analysis



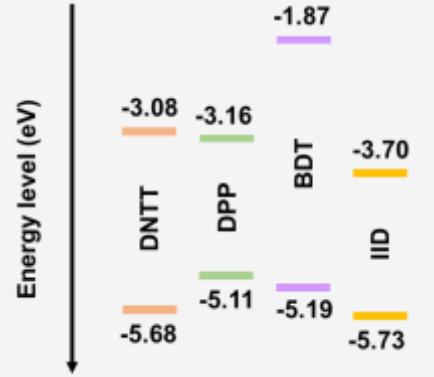
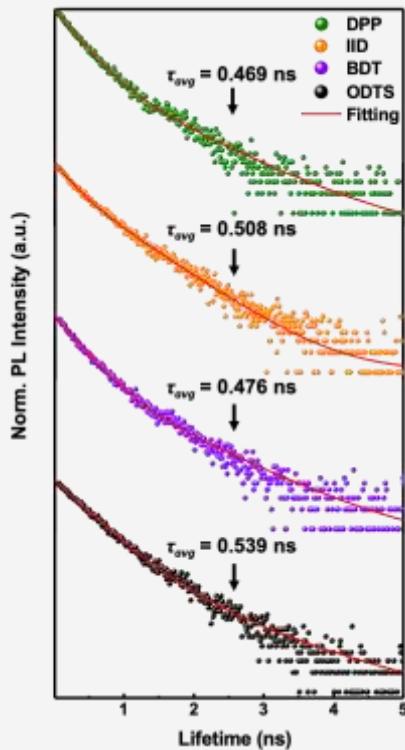
- Intermolecular interaction  $\Rightarrow$  aggregation
  - Roughness: DPP > BDT > IID > ODTs
- $\Rightarrow$  morphology of active layer was affected



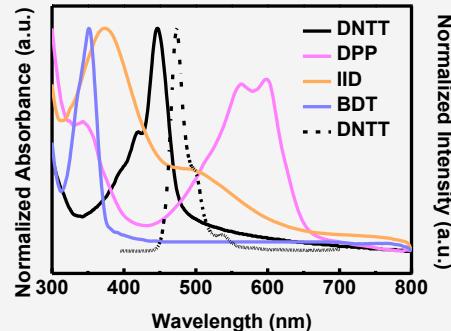
# Energy level and Optical Analysis



Exciton quenching and charge trapping



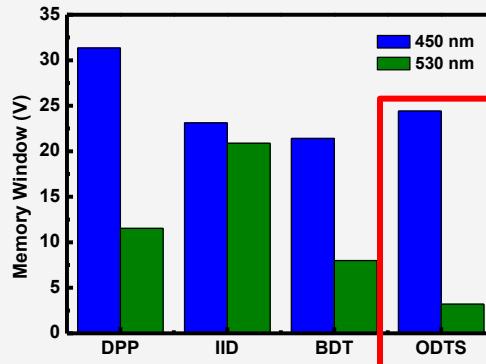
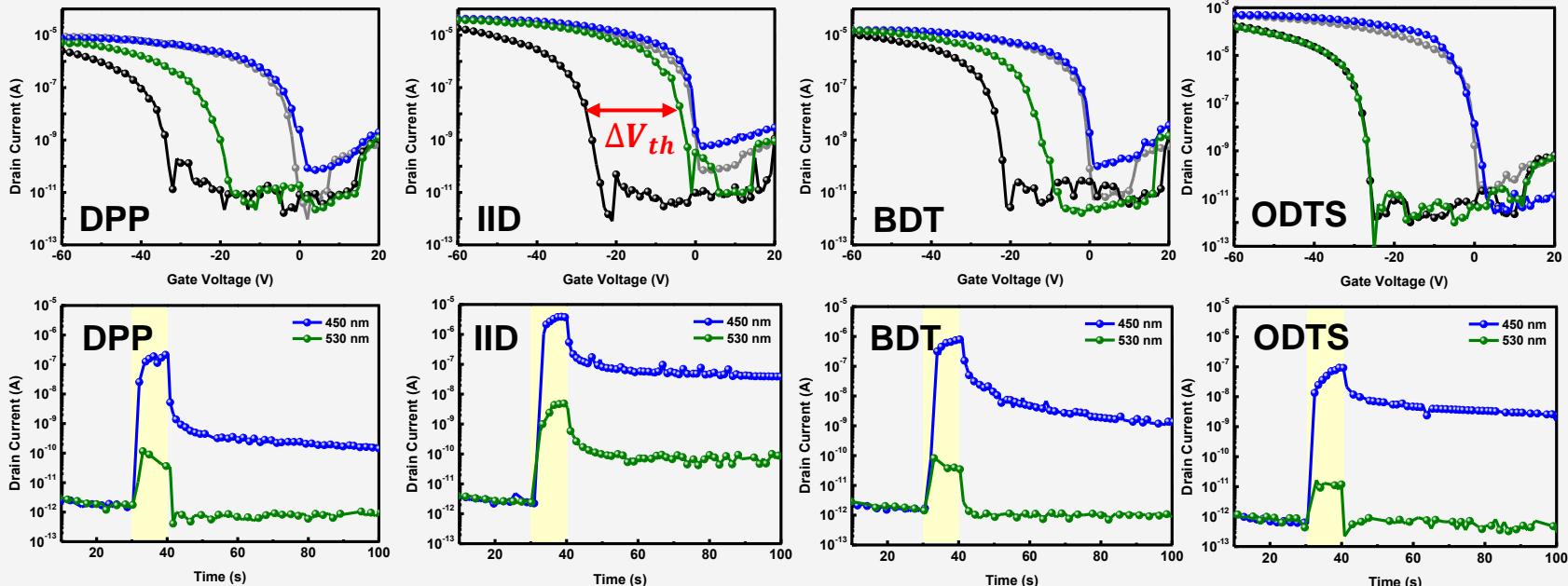
Strong donor—acceptor interaction  
⇒ unstable excitons



# Electrical Characteristic

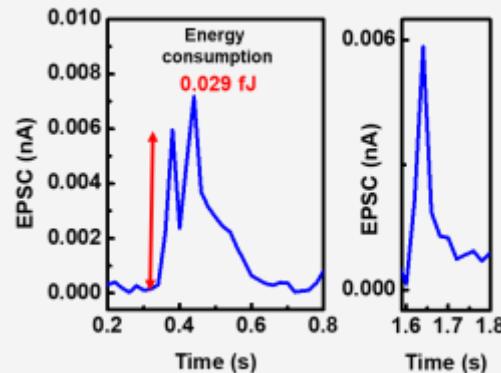
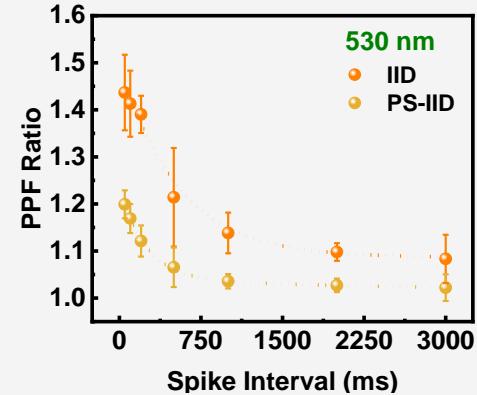
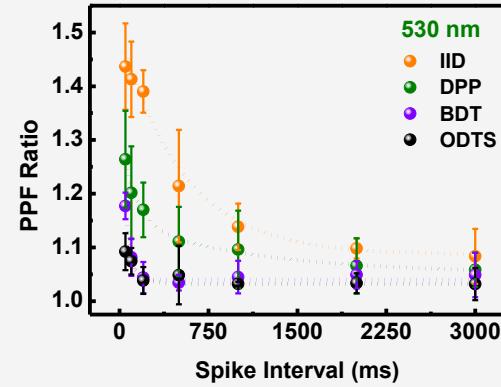
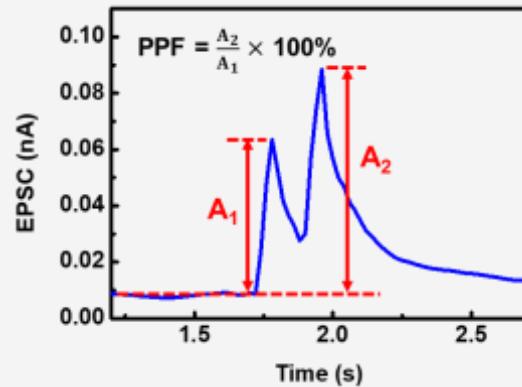
- IID shows the best photoresponsivity
- Short-term memory characteristic  $\Rightarrow$  Artificial synapse

● Initial    ● Writing,  $V_g = -70$  V, 1s  
● 450 nm, 10s    ● 530 nm, 10s



Effect of active layer for 450 nm

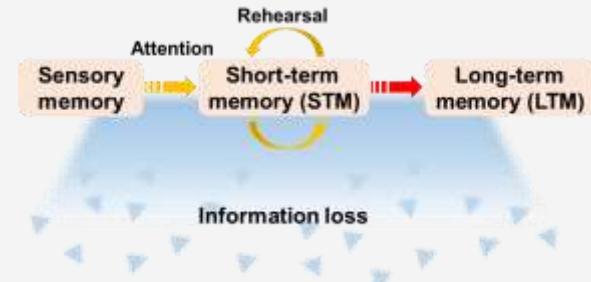
# Electrical Characteristic



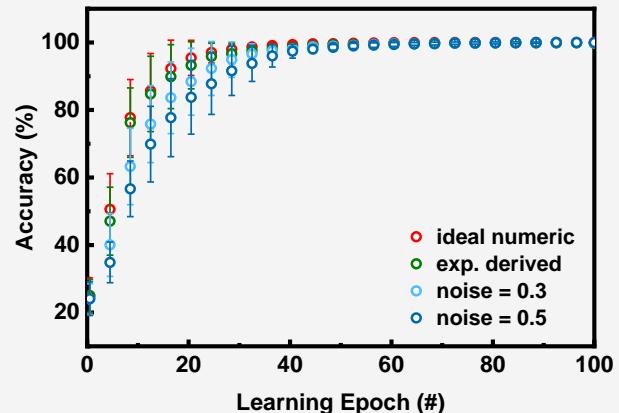
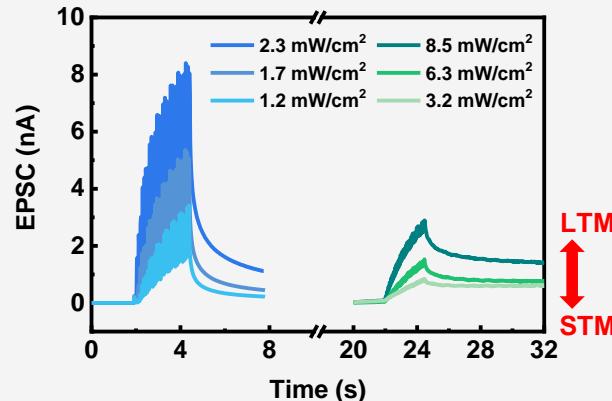
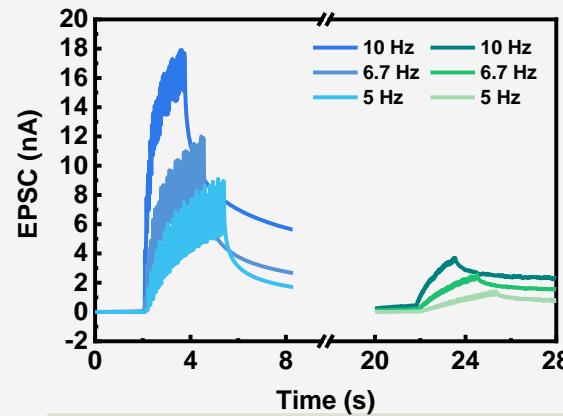
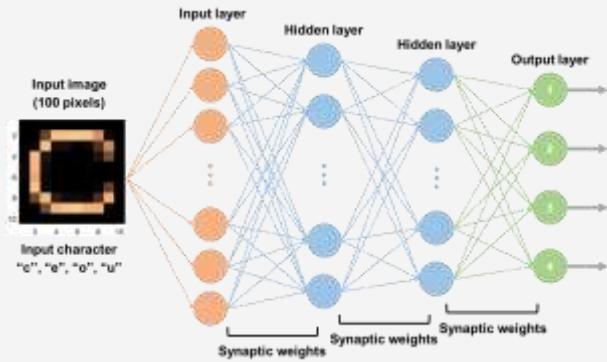
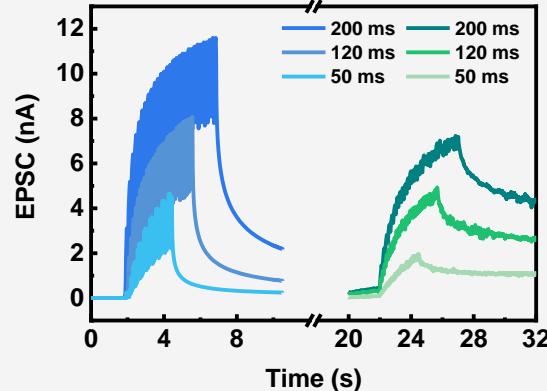
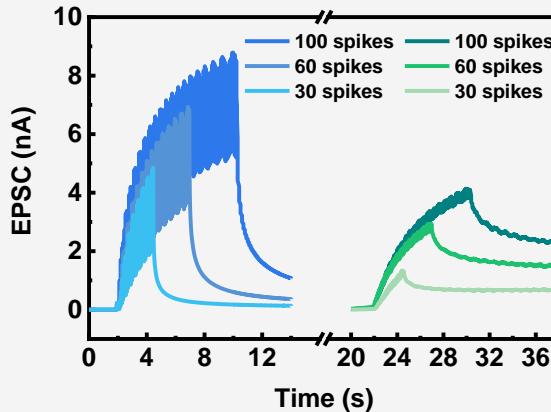
$$\text{Energy consumption} = V_d \times I \times t$$

$V_d$ : drain current  
 $I$ : EPSC of each spike  
 $t$ : spike width

Ultralow  $\Rightarrow 0.029$  fJ

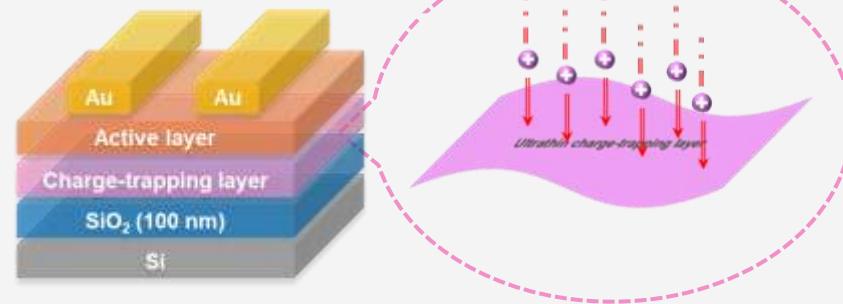


# Electrical Characteristic



# Conclusion

- 1 IID performs **STM to LTM behavior** in photosynaptic device
- 2 High PPF ratio is achieved using 530 nm  $\Rightarrow$  **144%**
- 3 Ultralow energy consumption is attained at low  $V_d \Rightarrow$  **0.029 fJ**
- 4 Recognition accuracy  $\Rightarrow$  **~100%**



# Thanks for your attention

Optoelectronic Polymer Laboratory

